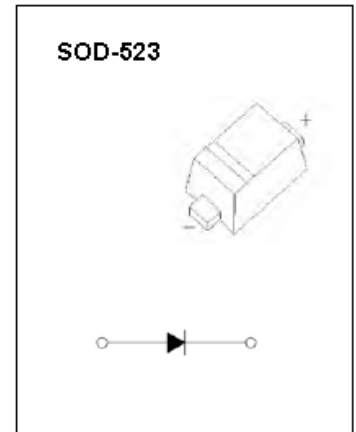
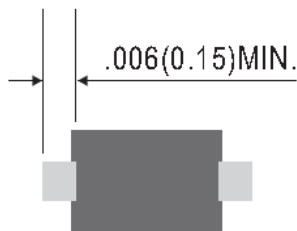
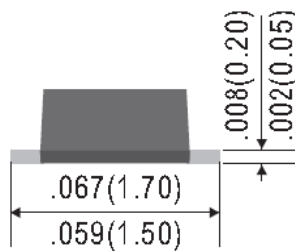
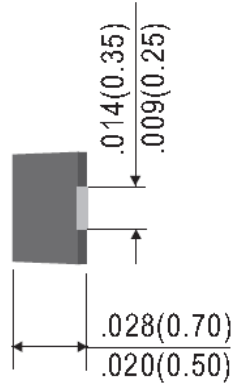
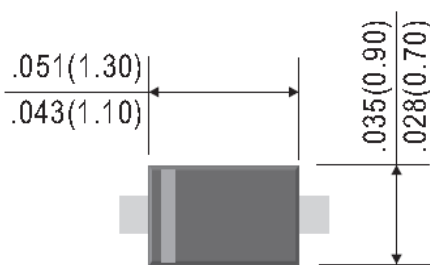




Dimensions in inches and (millimeters)

FEATURES

- High-Speed Switching Applications
- Lead Finish: 100% Matte Sn (Tin)
- Qualified Reflow Temperature: 260 °C
- Pb-Free package is available
- RoHS product for packing code suffix "G"
- Halogen free product for packing code suffix "H"
- Moisture Sensitivity Level 1
- Polarity: Color band denotes cathode end

MARKING: A6

Plastic-Encapsulate Diodes

Maximum Ratings (T _a =25°C unless otherwise noted)			
Parameter	Symbol	Limit	Unit
DC Reverse Voltage	V _R	75	V
Forward Current	I _F	200	mA
Peak Forward Surge Current	I _{FSM}	500	mA
Power Dissipation	P _D	150	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	833	°C/W
Junction temperature	T _J	150	°C
Operating/ Storage temperature	T _{STG}	-55~+150	°C

Electrical Characteristics (T _a =25°C unless otherwise noted)						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Reverse Voltage	V _(BR)	I _R = 100μA	75	—	—	V
Forward Voltage	V _{F1}	I _F =1mA	—	—	0.715	V
	V _{F2}	I _F =10mA	—	—	0.855	
	V _{F3}	I _F =50mA	—	—	1.00	
	V _{F4}	I _F =150mA	—	—	1.25	
Reverse Current	I _R	V _R =75V	—	—	1	μA
Reverse Recovery Time	t _{rr}	I _F =I _R =10mAdc I _{rr} =0.1XI _R , R _L =50Ω	—	—	6	ns
Forward Recovery Voltage	V _{FR}	I _F =10mA, t _r = 20ns	—	—	1.75	V
Diode Capacitance	C _D	V _R =0V, f=1MHz	—	—	2	pF
Stored Charge	Q _S	I _F =10mA, V _R =5.0V ,R _L =500Ω	—	—	45	pC

Typical Characteristics

